

3c760 U.S. PTO
10/001314
11/14/01

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10001314	FILING DATE 11/14/2001	CLASS 438	SUBCLASS -1.2	GAU 2812	EXAMINER
----------------------	---------------------------	--------------	------------------	-------------	--------------

****APPLICANTS:** Kim Chang; Kim Wan;

****CONTINUING DATA VERIFIED:**

BEST AVAILABLE COPY

**** FOREIGN APPLICATIONS VERIFIED:**
REPUBLIC OF KOREA 2001-15415 03/24/2001

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		TJK/ 204
Verified and Acknowledged Examiners's initials		
TITLE : Method for forming isolation layer of semiconductor device		

U.S. DEPT. OF COMM./PAT & TM-PTO-436 (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs. Drwg. Print Fig.
<input type="checkbox"/> TERMINAL DISCLAIMER		Applicati n Examiner	
		PREPARED FOR ISSUE	
WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.			

FILED WITH:

☐ DISK (CRF)

☐ CD-ROM

(Attached in pocket on right inside flap)